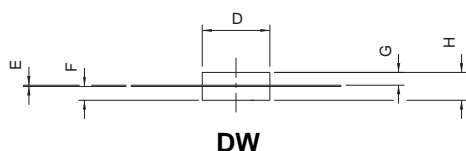
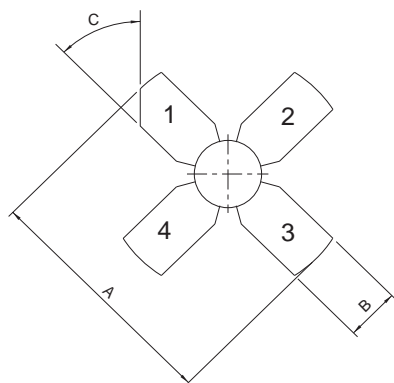


MECHANICAL DATA



PIN 1 DRAIN                      PIN 2 SOURCE  
 PIN 3 GATE                      PIN 4 SOURCE

| DIM | mm    | Tol. | Inches | Tol.  |
|-----|-------|------|--------|-------|
| A   | 26.16 | 0.38 | 1.030  | 0.015 |
| B   | 5.72  | 0.13 | 0.225  | 0.005 |
| C   | 45°   | 5°   | 45°    | 5°    |
| D   | 7.11  | 0.13 | 0.280  | 0.005 |
| E   | 0.13  | 0.03 | 0.005  | 0.001 |
| F   | 1.52  | 0.13 | 0.055  | 0.005 |
| G   | 0.43  | 0.20 | 0.060  | 0.008 |
| H   | 7.67  | REF  | 0.120  | REF   |

**GOLD METALLISED  
 MULTI-PURPOSE SILICON  
 DMOS RF FET  
 2.5W – 28V – 400MHz  
 SINGLE ENDED**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW  $C_{rss}$
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 13 dB MINIMUM

APPLICATIONS

- VHF/UHF COMMUNICATIONS  
 from DC to 1GHz

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

|              |  |                         |
|--------------|--|-------------------------|
| $P_D$        | Power Dissipation                      | 17.5W                   |
| $BV_{DSS}$   | Drain – Source Breakdown Voltage       | 65V                     |
| $BV_{GSS}$   | Gate – Source Breakdown Voltage        | $\pm 20V$               |
| $I_{D(sat)}$ | Drain Current                          | 1A                      |
| $T_{stg}$    | Storage Temperature                    | $-65$ to $150^{\circ}C$ |
| $T_j$        | Maximum Operating Junction Temperature | $200^{\circ}C$          |

**ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

| Parameter                                 | Test Conditions                          | Min. | Typ. | Max. | Unit    |
|---|--|------|------|------|---------|
| $BV_{DSS}$ Drain-Source Breakdown Voltage | $V_{GS} = 0$ $I_D = 10mA$                | 65   |      |      | V       |
| $I_{DSS}$ Zero Gate Voltage Drain Current | $V_{DS} = 28V$ $V_{GS} = 0$              |      |      | 1    | mA      |
| $I_{GSS}$ Gate Leakage Current            | $V_{GS} = 20V$ $V_{DS} = 0$              |      |      | 1    | $\mu A$ |
| $V_{GS(th)}$ Gate Threshold Voltage*      | $I_D = 10mA$ $V_{DS} = V_{GS}$           | 1    |      | 7    | V       |
| $g_{fs}$ Forward Transconductance*        | $V_{DS} = 10V$ $I_D = 0.2A$              | 0.18 |      |      | S       |
| $G_{PS}$ Common Source Power Gain         | $P_O = 2.5W$                             | 13   |      |      | dB      |
| $\eta$ Drain Efficiency                   | $V_{DS} = 28V$ $I_{DQ} = 0.1A$           | 40   |      |      | %       |
| VSWR Load Mismatch Tolerance              | $f = 400MHz$                             | 20:1 |      |      | —       |
| $C_{iss}$ Input Capacitance               | $V_{DS} = 28V$ $V_{GS} = -5V$ $f = 1MHz$ |      |      | 12   | pF      |
| $C_{oss}$ Output Capacitance              | $V_{DS} = 28V$ $V_{GS} = 0$ $f = 1MHz$   |      |      | 6    | pF      |
| $C_{rss}$ Reverse Transfer Capacitance    | $V_{DS} = 28V$ $V_{GS} = 0$ $f = 1MHz$   |      |      | 0.5  | pF      |

\* Pulse Test: Pulse Duration = 300  $\mu s$  , Duty Cycle  $\leq 2\%$

**HAZARDOUS MATERIAL WARNING**

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

**THERMAL DATA**

|                |                                    |               |
|----------------|------------------------------------|---------------|
| $R_{THj-case}$ | Thermal Resistance Junction – Case | Max. 10°C / W |
|----------------|------------------------------------|---------------|